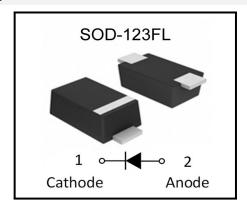


**Package** 

**Fast Recovery Rectifier Diode** 

#### **Features**

- Low forward voltage drop
- · High current capability
- · High reliability
- High surge current capability



### Description

· Case: molded plastic

• Polarity: Color band denotes cathode

• Package: SOD-123FL Plastic Package

#### **Making Code**



#### **Ordering information**

Part Number	ES1A	ES1B	ES1D	ES1G	ES1J
Marking	ES1A	ES1B	ES1D	ES1G	ES1J
Base qty	3K	3K	3K	3K	3K





Fast Recovery Rectifier Diode

### Maximum Ratings (@T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter		ES1B	ES1D	ES1G	ES1J	Unit
$V_{RRM}$	Maximum Recurrent Peak Reverse Voltage		100	200	400	600	V
V <sub>RMS</sub>	Maximum RMS Voltage		70	140	280	420	V
V <sub>DC</sub>	Maximum DC Blocking Voltage		100	200	400	600	V
	Maximum Average Forward Rectified		4.0				
$I_{(AV)}$	Current at T <sub>A</sub> = 55°C		1.0				A
Peak Forward Surge Current 8.3ms Single half sine-		30			A		
I <sub>FSM</sub>	wave Superimposed on Rated Load(JEDEC Method)		30				_ ^
$V_{F}$	Peak Forward Voltage at 1.0A DC		0.95		1.25	1.70	V
I <sub>R</sub>	Maximum DC Reverse Current T <sub>J</sub> = 25°C		5.0			uA	
чR	at Rated DC Blocking Voltage T <sub>J</sub> = 100°C		100				uA.
T <sub>RR</sub>	Maximum Reverse Recovery Time(Note1)	35		nS			
CJ	Typical Junction Capacitance(Note2)		15				pF
R <sub>θJA</sub>	Typical Thermal Resistance		80			°C/W	
T <sub>J</sub>	Operating Temperature Range		-55 to +150				°C
T <sub>STG</sub>	Storage Temperature Range		-55 to +150			°C	

Notes:(1)Measured with  $I_F$ =0.5A, $I_R$ =1A, $I_{RR}$ =0.25A

(2)Measured at 1.0 MHz and applied reverse voltage of 4.0V DC





Fast Recovery Rectifier Diode

Typical Performance Characteristics(T<sub>J</sub> = 25 °C, unless otherwise noted)

**Figure 1: Typical Forward Characteristics** 

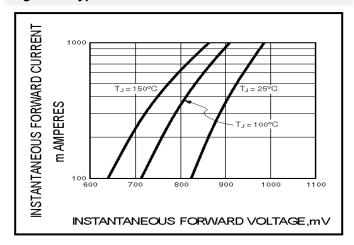


Figure 2: Typical Junction Capacitance

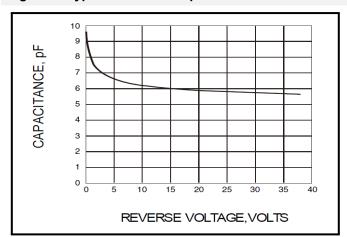
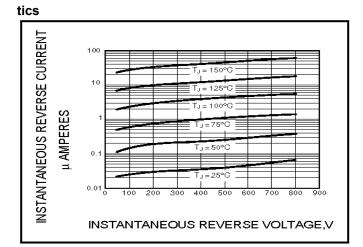
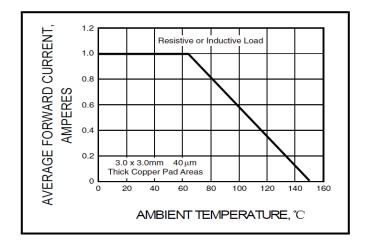


Figure 3: Typical Instantaneous Reverse Characteris-

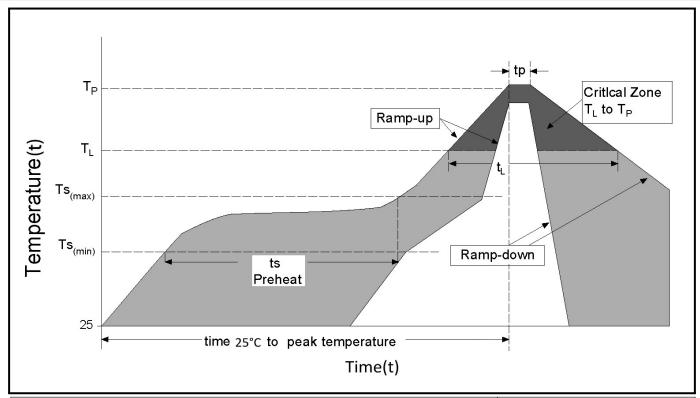
**Figure 4: Forward Drating Curve** 





Fast Recovery Rectifier Diode

### **Soldering Parameters**

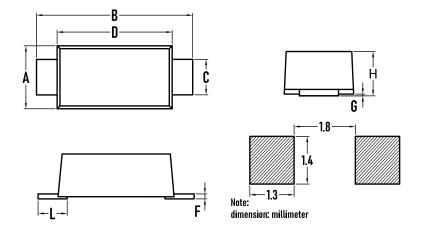


Reflow 0	Lead-free assembly		
	- Temperature Min (T <sub>S</sub> (min))	150°C	
Pre Heat	- Temperature Max (T <sub>S</sub> (max))	200°C	
	- Time (min to max) (t <sub>S</sub> )	60 - 180 secs	
Average ramp up rate (Liquidus Temp (T <sub>L</sub> ) to peak)		3°C/second max	
T <sub>S</sub> (max) to T <sub>L</sub> - Ramp-up Rate		3°C/second max	
Reflow	- Temperature (T <sub>L</sub> ) (Liquidus)	217°C	
	- Time (t <sub>L</sub> )	60 -150 secs	
Peak Temp	260 <sup>+0/-5°C</sup>		
Time within 5°C of actual peak Temperature (t <sub>p</sub> )		20 -40 secs	
Ramp-down Rate		6°C/second max	
Time 25°C to peak Temperature (t)		8 minutes Max.	
Do not exceed		260°C	



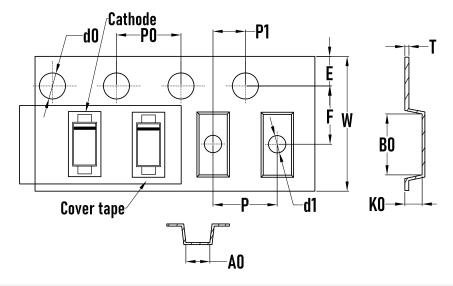
#### Fast Recovery Rectifier Diode

### Package Mechanical Data - SOD-123FL



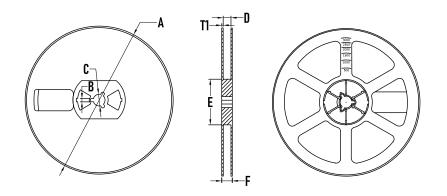
SYMBOL	MILLIMETER				
STIVIBUL	MIN.	Тур.	MAX.		
Α	1.50	1.75	2.00		
В	3.40	3.65	3.90		
С	0.70	0.95	1.20		
D	2.50	2.70	2.90		
F	0.05	0.15	0.26		
G	0.00	_	0.10		
Н	0.95	1.15	1.35		
L	0.35	0.63	0.90		

### Packaging Tape - SOD-123FL



SYMBOL	MILLIMETER
A0	2.10±0.1
В0	4.0 ±0.1
d0	1.5±0.1
d1	1.0±0.1
E	1.75±0.1
F	3.50±0.1
K0	1.25±0.1
Р	4.00±0.1
P0	4.00±0.1
P1	2.00±0.1
W	8.00±0.1
Т	0.2±0.02

### **Packaging Reel**



SYMBOL	MILLIMETER		
Α	177.8±0.2		
В	2.7±0.2		
С	13.5±0.2		
D	9.6±0.3		
E	54.5±0.2		
F	12.3±0.3		
T1	1.0±0.2		
Quantity	3000PCS		

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